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Applications of "<u>Embedded - Microcontrollers</u>"

D-4-ii-	
Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	35
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-TQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg322f64g-b-qfp48



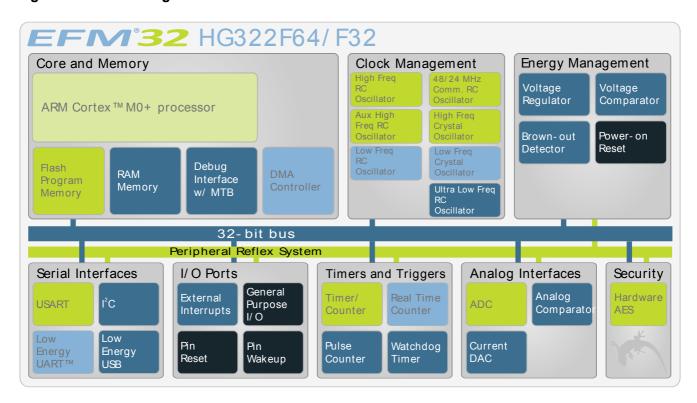
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M0+, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32HG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32HG322 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32HG Reference Manual*.

A block diagram of the EFM32HG322 is shown in Figure 2.1 (p. 3).

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M0+ Core

The ARM Cortex-M0+ includes a 32-bit RISC processor which can achieve as much as 0.9 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M0+ is described in detail in *ARM Cortex-M0+ Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and a Micro Trace Buffer (MTB) for data/instruction tracing.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32HG microcontroller. The flash memory is readable and writable from both the Cortex-M0+ and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits.



2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 4 external pins and 6 internal signals.

2.1.21 Current Digital to Analog Converter (IDAC)

The current digital to analog converter can source or sink a configurable constant current, which can be output on, or sinked from pin or ADC. The current is configurable with several ranges of various step sizes.

2.1.22 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.23 General Purpose Input/Output (GPIO)

In the EFM32HG322, there are 35 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32HG322 is a subset of the feature set described in the EFM32HG Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M0+	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO,
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
СМИ	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
USB	Full configuration	USB_VREGI, USB_VREGO, USB_DM, USB_DMPU, USB_DP
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	Full configuration with IrDA and I2S	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S and IrDA	US1_TX, US1_RX, US1_CLK, US1_CS



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB} =25°C and V_{DD} =3.0 V, as defined in Table 3.2 (p. 8), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T _{STG}	Storage tempera- ture range		-40		150 ¹	°C
T _S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V _{DDMAX}	External main sup- ply voltage		0		3.8	V
V _{IOPIN}	Voltage on any I/O pin		-0.3		V _{DD} +0.3	V

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

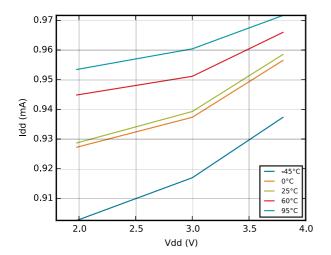
3.3.1 General Operating Conditions

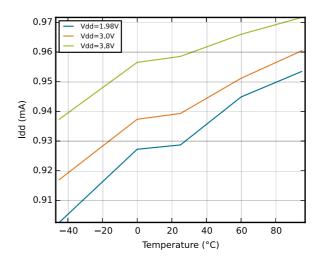
Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
T _{AMB}	Ambient temperature range	-40		85	°C
V _{DDOP}	Operating supply voltage	1.98		3.8	V
f _{APB}	Internal APB clock frequency			25	MHz
f _{AHB}	Internal AHB clock frequency			25	MHz



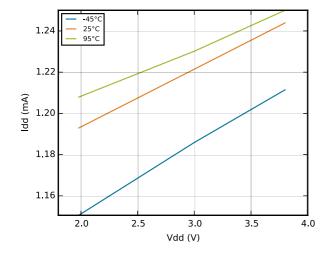
Figure 3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 6.6 MHz





3.4.2 EM1 Current Consumption

Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 24 MHz



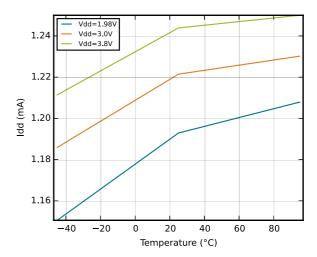
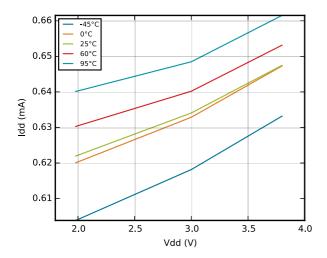




Figure 3.9. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11 MHz



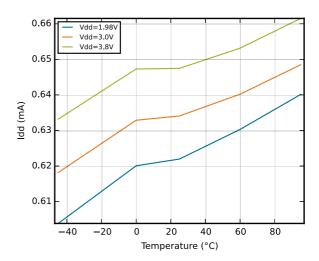
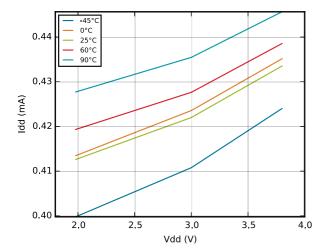
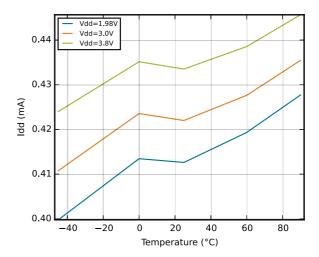


Figure 3.10. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6 MHz







Symbol	Parameter	Condition	Min	Тур	Max	Unit
R _{PD}	I/O pin pull-down resistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
t _{IOGLITCH}	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t _{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capaci- tance C _L =12.5-25pF.	20+0.1C _L		250	ns
	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C _L =350-600pF	20+0.1C _L		250	ns
V _{IOHYST}	I/O pin hysteresis (V _{IOTHR+} - V _{IOTHR-})	V _{DD} = 1.98 - 3.8 V	0.1V _{DD}			V

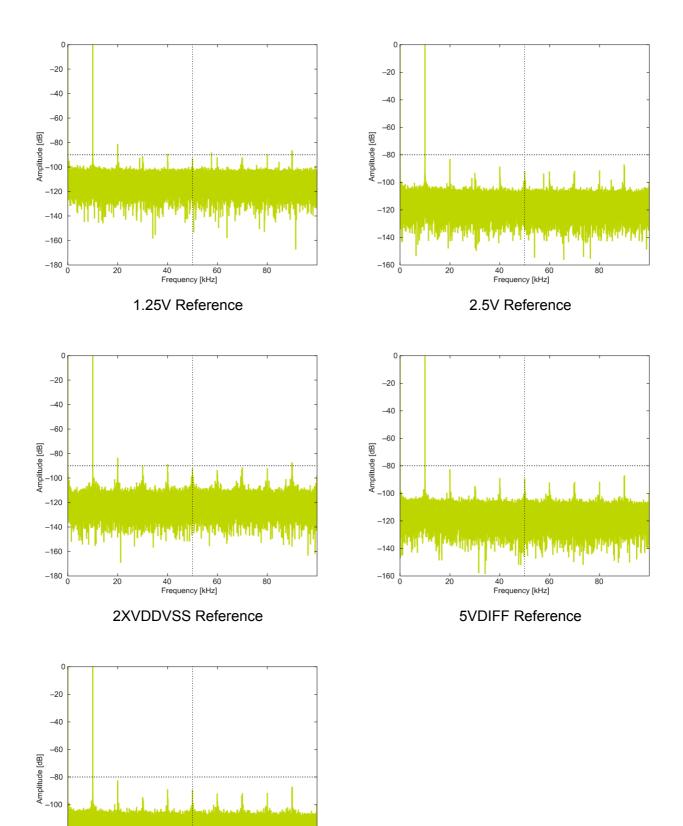


Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ADCREFIN_CH6}	Input range of ex- ternal positive ref- erence voltage on channel 6	See V _{ADCREFIN}	0.625		V_{DD}	V
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
		1 MSamples/s, 12 bit, external reference		392	510	μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b00		67		μΑ
I _{ADC}	Average active current	10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b01		63		μА
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b10		64		μА
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b11		244		μА
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μΑ
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resistance			10		kOhm
C _{ADCFILT}	Input RC filter/de- coupling capaci- tance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
		6 bit	7			ADC- CLK Cycles
t _{ADCCONV}	Conversion time	8 bit	11			ADC- CLK Cycles
		12 bit	13			ADC- CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC- CLK Cycles



3.10.1 Typical performance

Figure 3.28. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



VDD Reference

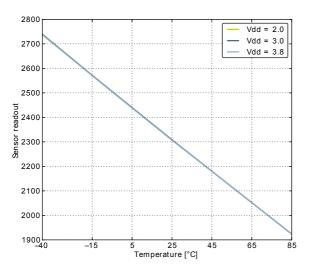
-120

-140

-160 L



Figure 3.33. ADC Temperature sensor readout



3.11 Current Digital Analog Converter (IDAC)

Table 3.16. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Тур	Max	Unit
1 .	Active current with	EM0, default settings		13.0		μΑ
I _{IDAC}	STEPSEL=0x10	Duty-cycled		10		nA
I _{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		μА
I _{STEP}	Step size			0.05		μΑ
I _D	Current drop at high impedance load	V _{IDAC_OUT} = V _{DD} - 100mV		0.79		%
TC _{IDAC}	Temperature coefficient	V _{DD} = 3.0V, STEPSEL=0x10		0.3		nA/°C
VC _{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		11.7		nA/V

Table 3.17. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		15.1		μΑ
I _{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		μА
I _{STEP}	Step size			0.05		μΑ
I _D	Current drop at high impedance load	V _{IDAC_OUT} = 200 mV		0.30		%
TC _{IDAC}	Temperature coefficient	V _{DD} = 3.0 V, STEPSEL=0x10		0.2		nA/°C
VC _{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		12.5		nA/V



Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{0x10}	Nominal IDAC output current with STEPSEL=0x10			8.5		μА
I _{STEP}	Step size			0.5		μΑ
I _D	Current drop at high impedance load	V _{IDAC_OUT} = 200 mV		0.62		%
TC _{IDAC}	Temperature coefficient	V _{DD} = 3.0 V, STEPSEL=0x10		2.8		nA/°C
VC _{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		94.4		nA/V

Table 3.22. IDAC Range 3 Source

Symbol	Parameter	Condition	Min	Тур	Max	Unit
1 .	Active current with	EM0, default settings		18.7		μΑ
IDAC	STEPSEL=0x10	Duty-cycled		10		nA
I _{0x10}	Nominal IDAC output current with STEPSEL=0x10			33.9		μΑ
I _{STEP}	Step size			2.0		μA
I _D	Current drop at high impedance load	V _{IDAC_OUT} = V _{DD} - 100 mV		3.54		%
TC _{IDAC}	Temperature coefficient	V _{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC _{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		159.5		nA/V

Table 3.23. IDAC Range 3 Sink

Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		62.5		μΑ
I _{0x10}	Nominal IDAC output current with STEPSEL=0x10			34.1		μΑ
I _{STEP}	Step size			2.0		μA
I _D	Current drop at high impedance load	V _{IDAC_OUT} = 200 mV		1.75		%
TC _{IDAC}	Temperature coefficient	V _{DD} = 3.0 V, STEPSEL=0x10		10.9		nA/°C
VC _{IDAC}	Voltage coefficient	T = 25 °C, STEPSEL=0x10		148.6		nA/V

Table 3.24. IDAC

Symbol	Parameter	Min	Тур	Max	Unit
t _{IDACSTART}	Start-up time, from enabled to output settled		40		μs



Figure 3.34. IDAC Source Current as a function of voltage on IDAC_OUT

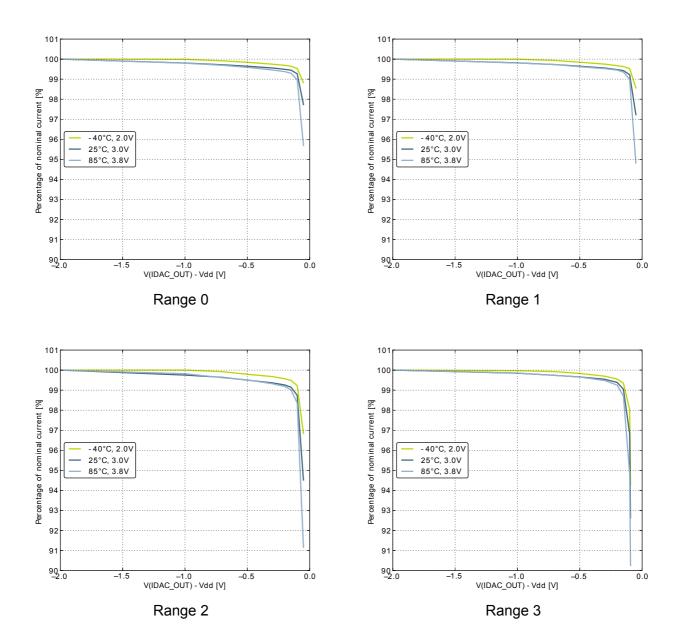




Table 3.28. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		400 ¹	kHz
t _{LOW}	SCL clock low time	1.3			μs
t _{HIGH}	SCL clock high time	0.6			μs
t _{SU,DAT}	SDA set-up time	100			ns
t _{HD,DAT}	SDA hold time	8		900 ^{2,3}	ns
t _{SU,STA}	Repeated START condition set-up time	0.6			μs
t _{HD,STA}	(Repeated) START condition hold time	0.6			μs
t _{SU,STO}	STOP condition set-up time	0.6			μs
t _{BUF}	Bus free time between a STOP and START condition	1.3			μs

¹For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32HG Reference Manual.

Table 3.29. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Тур	Max	Unit
f _{SCL}	SCL clock frequency	0		1000 ¹	kHz
t _{LOW}	SCL clock low time	0.5			μs
t _{HIGH}	SCL clock high time	0.26			μs
t _{SU,DAT}	SDA set-up time	50			ns
t _{HD,DAT}	SDA hold time	8			ns
t _{SU,STA}	Repeated START condition set-up time	0.26			μs
t _{HD,STA}	(Repeated) START condition hold time	0.26			μs
t _{SU,STO}	STOP condition set-up time	0.26			μs
t _{BUF}	Bus free time between a STOP and START condition	0.5			μs

¹For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32HG Reference Manual.

3.15 USB

The USB hardware in the EFM32HG322 passes all tests for USB 2.0 Full Speed certification. The test report will be distributed with application note "AN0046 - USB Hardware Design Guide" when ready.

Table 3.30. USB

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{USBOUT}	USB regulator output voltage		3.1	3.4	3.7	V
LUCDOUT	USB regulator output current	BIASPROG=0, T _{AMB} =25°C	55.7	79.4	104.1	mA
		BIASPROG=1, T _{AMB} =25°C	66.0	95.9	126.4	mA
		BIASPROG=2, T _{AMB} =25°C	94.6	146.5	188.1	mA
		BIASPROG=3, T _{AMB} =25°C	80.4	128.3	176.0	mA

²The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

³When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10⁻⁹ [s] * f_{HFPERCLK} [Hz]) - 5).



4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32HG322.

4.1 Pinout

The *EFM32HG322* pinout is shown in Figure 4.1 (p. 52) and Table 4.1 (p. 52). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32HG322 Pinout (top view, not to scale)

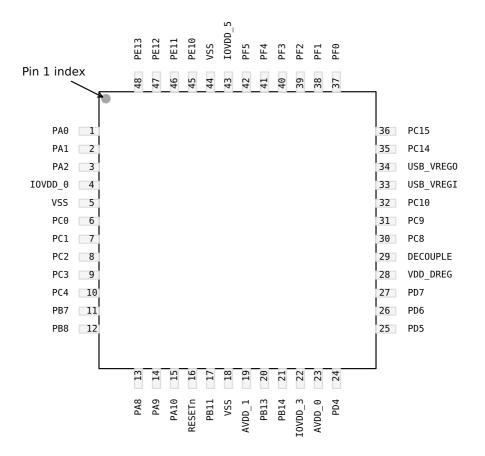


Table 4.1. Device Pinout

	QFP48 Pin# and Name		Pin Alternate Function		
Pin #	Pin Name	Analog	Timers	Communication	Other
1	PA0		TIM0_CC1 #6 TIM0_CC0 #0/1/4 PCNT0_S0IN #4	USB_DMPU #0 US1_RX #4 LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 PRS_CH3 #3 GPIO_EM4WU0
2	PA1		TIM0_CC0 #6 TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0



Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
TIM0_CC2	PA2	PA2			PC1	PF2	PF2	Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI0					PC2	PF3		Timer 0 Complimentary Deat Time Insertion channel 0.
TIM0_CDTI1		PC14			PC3	PF4	PC14	Timer 0 Complimentary Deat Time Insertion channel 1.
TIM0_CDTI2		PC15			PC4	PF5	PC15	Timer 0 Complimentary Deat Time Insertion channel 2.
TIM1_CC0		PE10		PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11		PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11				Timer 1 Capture Compare input / output channel 2.
TIM2_CC0	PA8		PC8	PF2				Timer 2 Capture Compare input / output channel 0.
TIM2_CC1	PA9		PC9	PE12				Timer 2 Capture Compare input / output channel 1.
TIM2_CC2	PA10		PC10	PE13				Timer 2 Capture Compare input / output channel 2.
US0_CLK	PE12		PC9	PC15	PB13	PB13	PE12	USART0 clock input / output.
US0_CS	PE13		PC8	PC14	PB14	PB14	PE13	USART0 chip select input / output.
								USART0 Asynchronous Receive.
US0_RX	PE11		PC10	PE12	PB8	PC1	PC1	USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX	PE10			PE13	PB7	PC0	PC0	USART0 Asynchronous Transmit.Also used as receive input in half duplex communication.
000_1X	1210			1 213		1 00	100	USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0	PC15	PB11	PC3		USART1 clock input / output.
US1_CS	PB8		PF1	PC14	PC14	PC0		USART1 chip select input / output.
								USART1 Asynchronous Receive.
US1_RX	PC1		PD6	PD6	PA0	PC2		USART1 Synchronous mode Master Input / Slave Output (MISO).
LIC4 TV	PC0		PD7	PD7	PF2	PC1		USART1 Asynchronous Transmit.Also used as receive input in half duplex communication.
US1_TX	PCU		PD/	PD/	FFZ	FOI		USART1 Synchronous mode Master Output / Slave Input (MOSI).
USB_DM	PC14							USB D- pin.
USB_DMPU	PA0							USB D- Pullup control.
USB_DP	PC15							USB D+ pin.
USB_VREGI	USB_VREGI							USB Input to internal 3.3 V regulator
USB_VREGO	USB_VREGO							USB Decoupling for internal 3.3 V USB regulator and regulator output

4.3 GPIO Pinout Overview

The specific GPIO pins available in EFM32HG322 is shown in Table 4.3 (p. 57). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

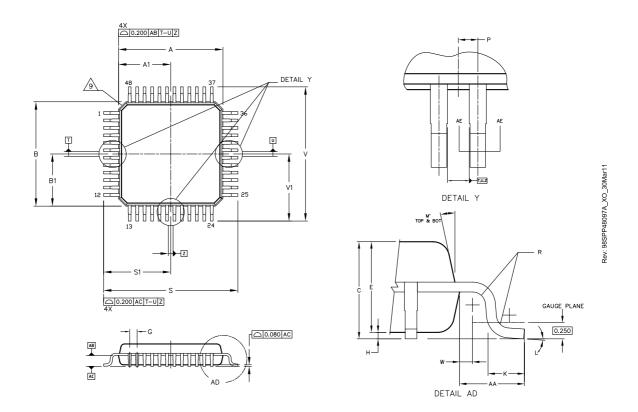


Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	PA10	PA9	PA8	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	-	-	-	PC10	PC9	PC8	-	-	-	PC4	PC3	PC2	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	PD4	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	PF5	PF4	PF3	PF2	PF1	PF0

4.4 TQFP48 Package

Figure 4.2. TQFP48



Note:

- 1. Dimensions and tolerance per ASME Y14.5M-1994
- 2. Control dimension: Millimeter.
- 3. Datum plane AB is located at bottom of lead and is coincident with the lead where the lead exists from the plastic body at the bottom of the parting line.
- 4. Datums T, U and Z to be determined at datum plane AB.
- 5. Dimensions S and V to be determined at seating plane AC.
- 6. Dimensions A and B do not include mold protrusion. Allowable protrusion is 0.250 per side. Dimensions A and B do include mold mismatch and are determined at datum AB.
- 7. Dimension D does not include dambar protrusion. Dambar protrusion shall not cause the D dimension to exceed 0.350.
- 8. Minimum solder plate thickness shall be 0.0076.

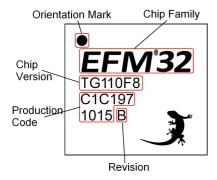


6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 62).

6.3 Errata

Please see the errata document for EFM32HG322 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:

http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit



7 Revision History

7.1 Revision 1.00

December 4th, 2015

Updated all specs with results of full characterization.

Updated part number to revision B.

Added the USB electrical specifications table.

7.2 Revision 0.91

May 6th, 2015

Updated current consumption table for energy modes.

Updated GPIO max leakage current.

Updated startup time for HFXO and LFXO.

Updated current consumption for HFRCO and LFRCO.

Updated ADC current consumption.

Updated IDAC characteristics tables.

Updated ACMP internal resistance.

Updated VCMP current consumption.

7.3 Revision 0.90

March 16th, 2015

Note

This datasheet revision applies to a product under development. It's characteristics and specifications are subject to change without notice.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Updated GPIO electrical characteristics.

Updated Max ESR_{HFXO} value for Crystal Frequency of 25 MHz.

Updated LFRCO plots.

Updated HFRCO table and plots.

Updated ADC table and temp sensor plot.

Added DMA current in Digital Peripherals section.

Updated block diagram.

Corrected leadframe type to matte-Sn.



B Contact Information

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Please visit the Silicon Labs Technical Support web page: http://www.silabs.com/support/pages/contacttechnicalsupport.aspx and register to submit a technical support request.



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